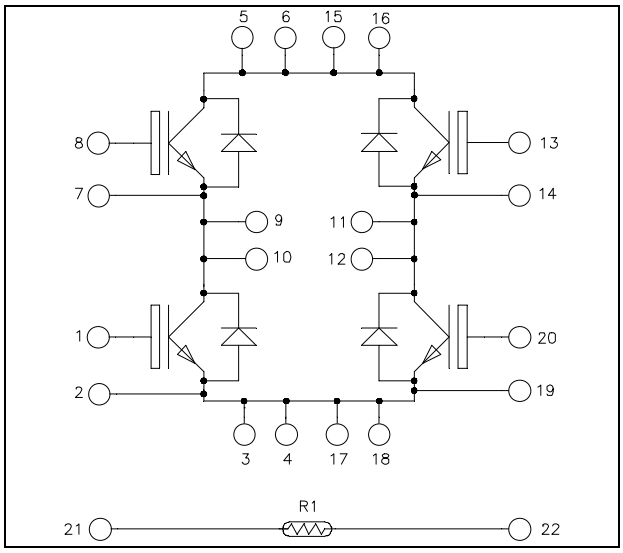
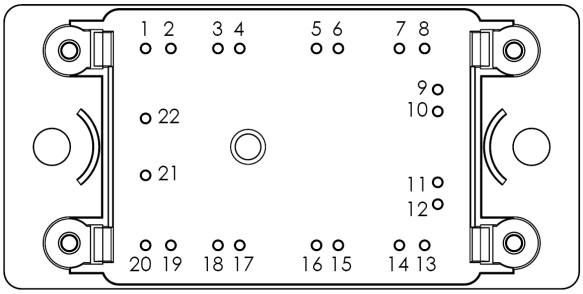
APTGFQ25H120T2G

Full - Bridge NPT IGBT Power Module

V_{CES} = 1200V
I_C = 25A @ Tc = 80°C





Pins 5/6/15/16 ; 3/4/17/18 ; 9/10 ; 11/12 must be shorted together

Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Fieldstop IGBT
  - Low voltage drop
  - short tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

All ratings @ T_j = 25°C unless otherwise specified

Absolute maximum ratings (per IGBT)

Symbol	*Parameter*		*Max ratings*	*Unit*
V_{CES}	Collector - Emitter Breakdown Voltage		1200	V
I_C	Continuous Collector Current	T_C = 25°C	40	A
		T_C = 80°C	25	
I_{CM}	Pulsed Collector Current	T_C = 25°C	50	
V_{GE}	Gate – Emitter Voltage		±20	V
P_D	Maximum Power Dissipation	T_C = 25°C	227	W
RBSOA	Reverse Bias Safe Operating Area	T_j = 125°C	50A@1150V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

Electrical Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	V_{GE} = 0V ; V_{CE} = 1200V				250	µA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	V_{GE} =15V I_C = 25A	T_j = 25°C		2.1		V
			T_j = 125°C		2.3		
$V_{GE(th)}$	Gate Threshold Voltage	V_{GE} = V_{CE} , I_C = 1mA		3	5.5	7	V
I_{GES}	Gate – Emitter Leakage Current	V_{GE} = 20V, V_{CE} = 0V				150	nA

Dynamic Characteristics (per IGBT)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
C_{ies}	Input Capacitance	V_{GE} = 0V V_{CE} = 25V f = 1MHz			2.02		nF
C_{oes}	Output Capacitance				0.19		
C_{res}	Reverse Transfer Capacitance				0.06		
Q_G	Gate charge	V_{GE}=-8/20V, I_C=25A V_{CE}=600V			280		nC
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) V_{GE} = 15V V_{Bus} = 600V I_C = 25A R_G = 16Ω			60		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				346		
T_f	Fall Time				40		
E_{on}	Turn-on Switching Energy	V_{GE} = 15V V_{Bus} = 600V I_C = 25A R_G = 16Ω	T_j = 125°C		1.35		mJ
E_{off}	Turn-off Switching Energy		T_j = 125°C		1.76		
I_{sc}	Short Circuit data	V_{GE} ≤15V ; V_{Bus} = 900V t_p ≤ 10µs ; T_j = 125°C			125		A
R_{thJC}	Junction to Case Thermal Resistance					0.55	°C/W

Reverse diode ratings and characteristics (per diode)

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	V_R=1200V				100	µA
I_F	DC Forward Current		Tc = 80°C		25		A
V_F	Diode Forward Voltage	I_F = 25A			2.6	3.1	V
		I_F = 50A			3.2		
		I_F = 25A	T_j = 125°C		1.8		
t_{rr}	Reverse Recovery Time	I_F = 25A V_R = 667V di/dt =200A/µs	T_j = 25°C		320		ns
			T_j = 125°C		360		
Q_{rr}	Reverse Recovery Charge		T_j = 25°C		480		nC
			T_j = 125°C		1800		
R_{thJC}	Junction to Case Thermal Resistance					1.4	°C/W

Temperature sensor NTC

Symbol	Characteristic	Min	Typ	Max	Unit
R_{25}	Resistance @ 25°C		22		kΩ
$\Delta R_{25}/R_{25}$	Resistance tolerance			5	%
$\Delta B/B$	Beta tolerance			3	
$B_{25/100}$	T_{25} = 298.16 K		3980		K

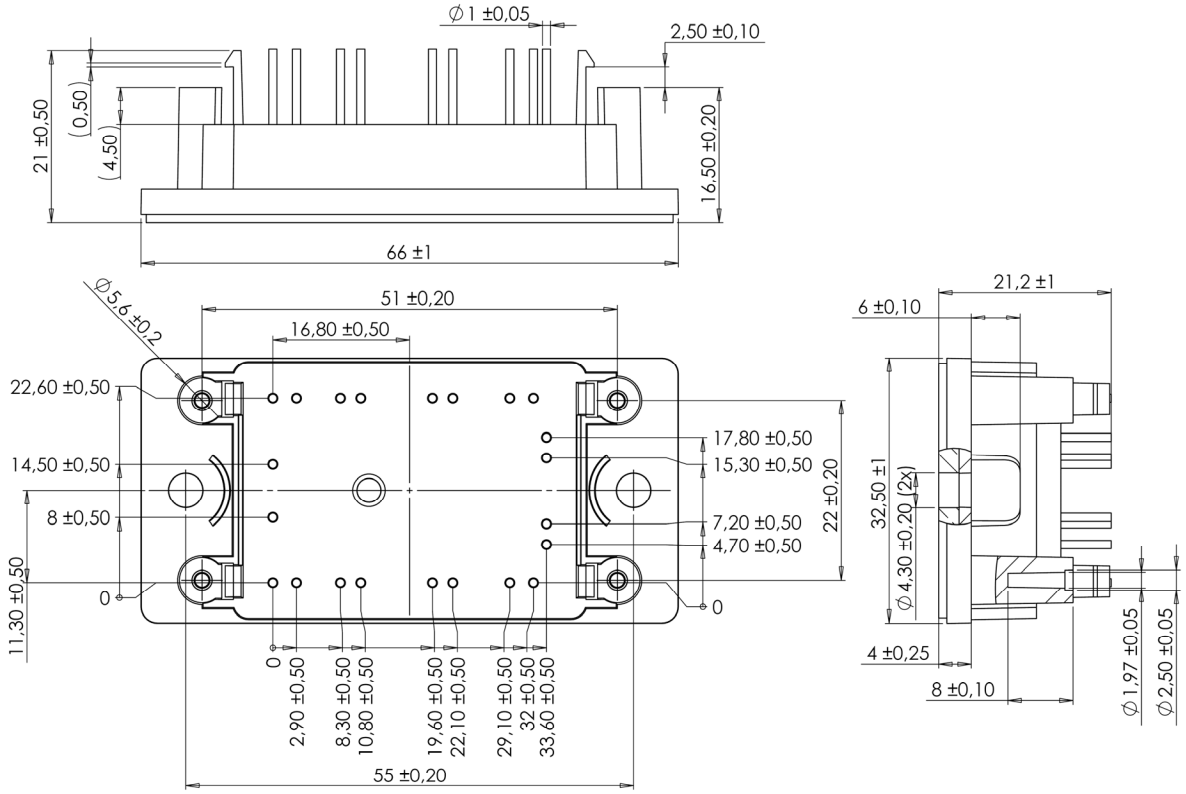
$$R_T = \frac{R_{25}}{\exp\left[B_{25/100}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

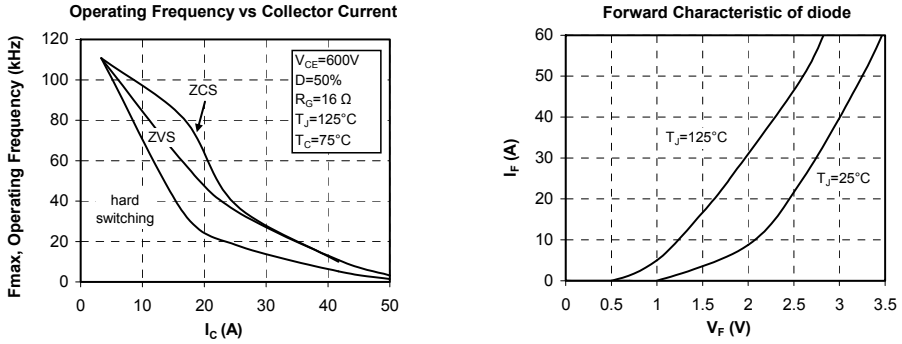
Thermal and package characteristics

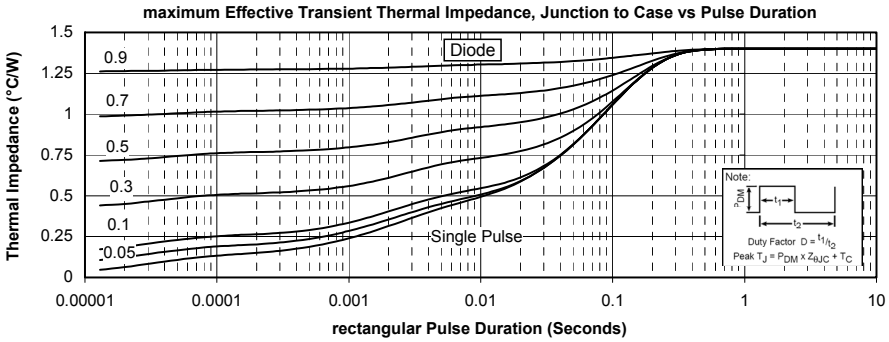
Symbol	Characteristic			Min	Typ	Max	Unit
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T_J	Operating junction temperature range			-40		150	°C
T_{STG}	Storage Temperature Range			-40		125	
T_C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M4	2		3	N.m
Wt	Package Weight					75	g

Package outline (dimensions in mm)

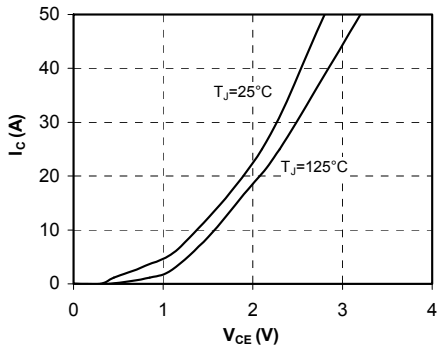


Typical Performance Curve

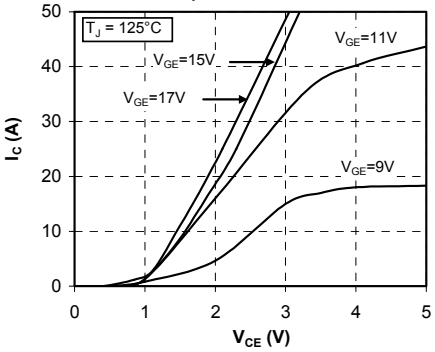




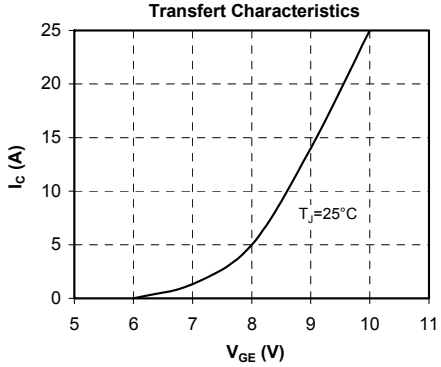
Output Characteristics (V_{GE}=15V)



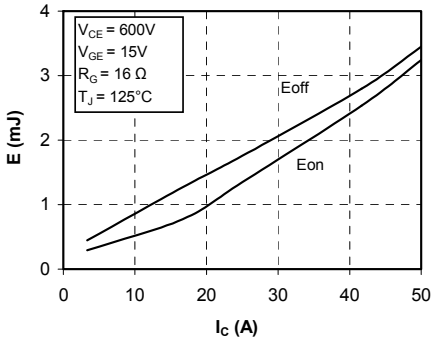
Output Characteristics



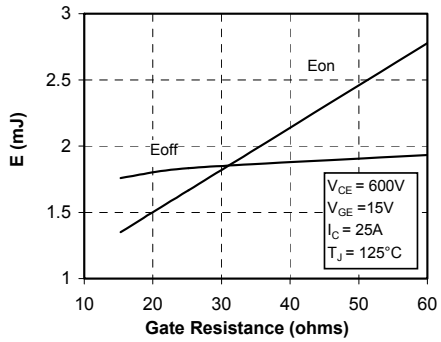
Transfert Characteristics



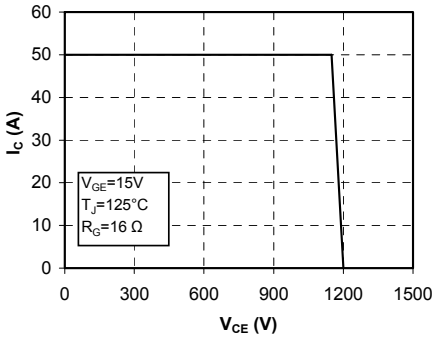
Energy losses vs Collector Current



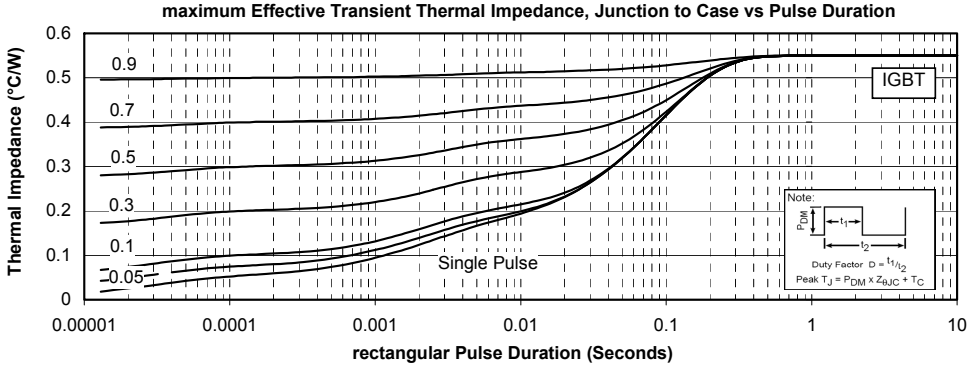
Switching Energy Losses vs Gate Resistance



Reverse Bias Safe Operating Area



maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration



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